



Bipolar NPN Bare Die – BTN6088

Part Description

The BTN6088 is a silicon BJT transistor available in bare die form and well suited for use in general purpose switching and amplifier applications.

Key Parameters:

- VCBO = 25V
- VCEO = 20V
- VEBO = 12V
- hFE = 400-2700 @ VCE = 3V, IC = 0.1A
- VCE(Sat) = 0.4V @ IC = 0.5A, IB = 20mA
- fT = 250 MHz @ VCE = 10V, IE = 0A
- COBO = 8pF @ VCB = 10V

Features

High VEBO. Designed to provide performance equivalent to Panasonic 2SD1328 or ROHM 2SD2114

Die Size (Unawn)

600 μ m X 600 μ m, 24 Mils X 24 Mils

This is a shortform datasheet only

For the full datasheet

Please contact sales@siliconsupplies.com

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